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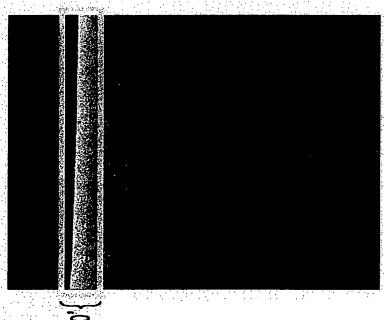
(a)

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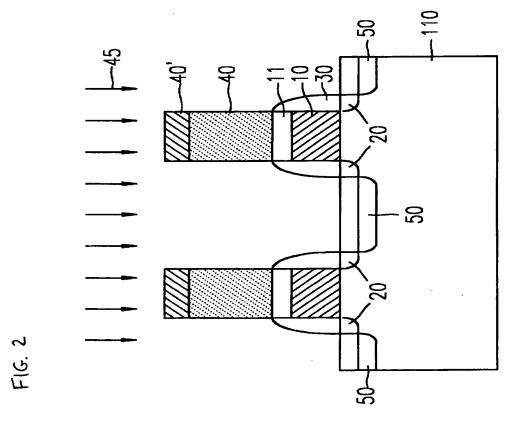
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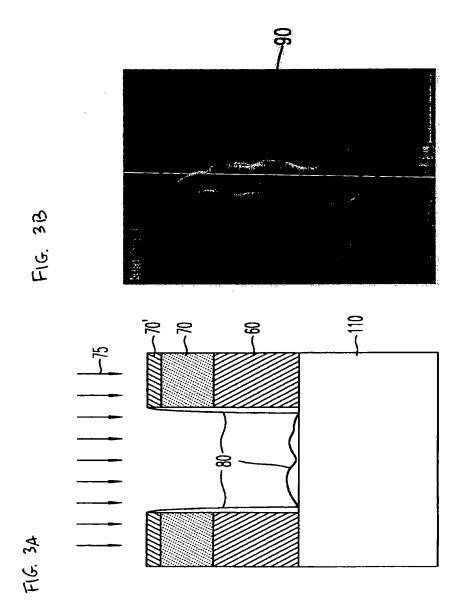
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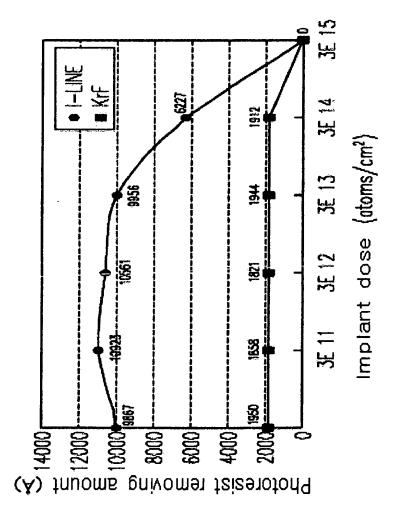
FIG. 1B

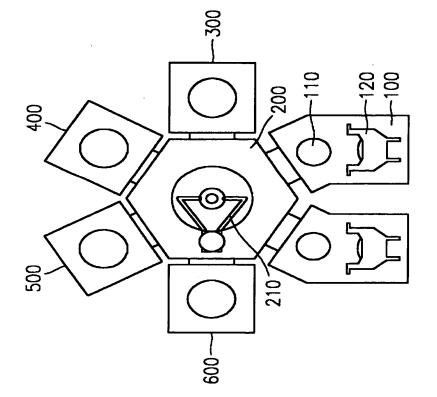


F1G. 1A



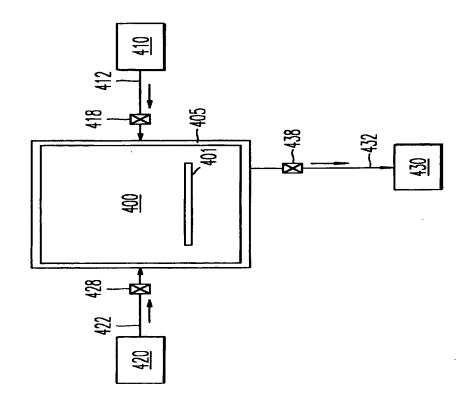






F(G. 5

F1G. 6



F16. 7

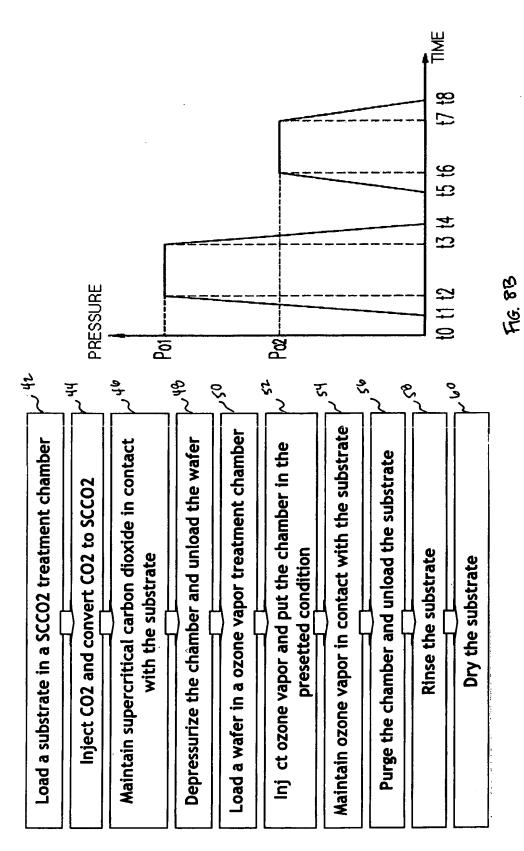


FIG. 84

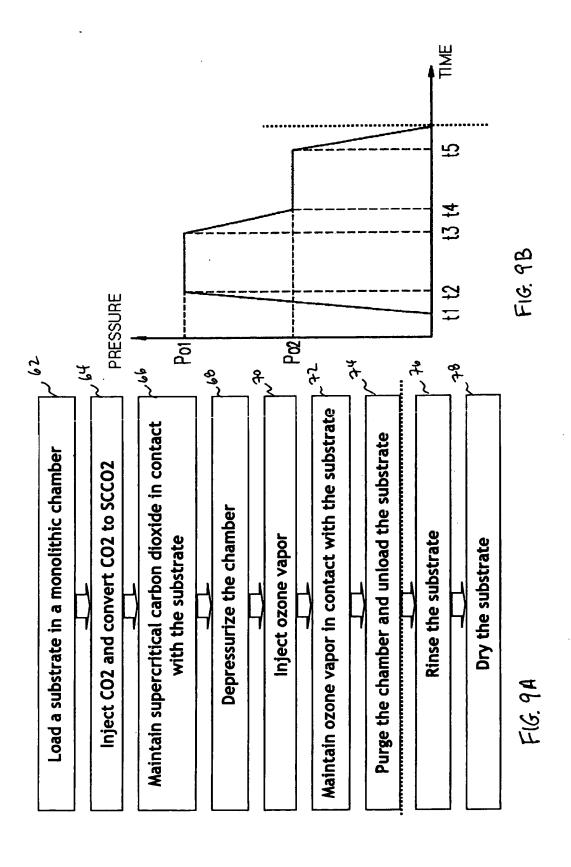


FIG. 10

	80%	900	_	8		at a	283	ere	
Place a wafer in a pressure chamber 1	Seal the pressure chamber 1		Pressurize the pressure chamber 1 with carbon dioxide		Convert carbon dioxide to supercritical carbon dioxide by increasing the pressure (73bar) and temperature (31°C*)	Maintain supercritical carbon dioxide in contact with the substrate at a temperature of about 100°C and a pressure of about 150bar to cause swelling, cracking and delimination of photoresist		Depressurize and vent the pressure chamber 1 to normal atmosphere	continued

	عبع ا	_
Transfer the wafer to a pressure chamber 2 Seal the pressure chamber 2 Pressurize the pressure chamber 2 to above 60kPa with ozone gas at a temperature of about 105°C* and water vapor at a temperature of about 115°C* Maintain reaction until photoresist is converted into water-soluble product	Rinse wafer	

*: temp of CO2, O3 and vapor